EAST - [10800792.wsp:1]

File View Edit Tools Window Help

- Drafts
  - BRS: memory and (storage near node
- Pending
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  - L1: (271) scalable near two-transistor near memory scalable near two near transistor near memory...
  - L2: (9) scalable near two-transistor near memory scalable near two near transistor near memory ne...
  - L3: (12) scalable near two-transistor near memory scalable near two near transistor near memory
  - L4: (5) memory and (memory near node storage near node) and tunnel near junction near barrier and...
  - L5: (9) memory and (memory near node storage near node) and tunnel near junction near barrier and...
  - L6: (211) memory and (memory near node storage near node) and barrier and (data near line data ne...
  - L7: (43) memory and (memory near node storage near node) and (tunnel near10 barrier) and (data ne...
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DBs | US-PGPUB; USPAT; I | Plurals

Default operator: OR | Highlight all hit terms initially

memory and (memory near node storage near node) and (tunnel near10 barrier) and (data near line data near electrode) and gate and (dielectric insulat$3)

BRS form | IS&R form | Image | Text | HTML

	U	1	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1	☐	☐	US 20050156225 A1	20050721	26	Methods of fabricating semiconductor devices with scalable two transistor memory cells	257/316	438/266
2	☐	☐	US 20050127429 A1	20050616	55	Semiconductor nonvolatile memory device	257/315	
3	☐	☐	US 20050030829 A1	20050210	47	Thin film magnetic memory device conducting data write operation by application of a magnetic field	365/232	
4	☐	☐	US 20040252576 A1	20041216	22	Semiconductor memory element arrangement	365/232	257/E21.68; 257/E27.103
5	☐	☐	US 20040238974 A1	20041202	26	Scalable two transistor memory devices and methods of fabrication therefor	257/314	257/900
6	☐	☐	US 20040227173.A1	20041118	27	Semiconductor devices with scalable two transistor memory cells and methods of fabricating the same	257/296	
7	☐	☐	US 20040170050 A1	20040902	27	Semiconductor integrated circuit device with improved storage MOSFET arrangement	365/149	
8	☐	☐	US 20040150022 A1	20040805	25	Semiconductor memory device having a multiple tunnel junction pattern and method of fabricating the same	257/296	257/E27.084
9	☐	☐	US 20040084714 A1	20040506	43	Semiconductor memory device	257/315	257/E21.682; 257/E27.103; 257/E29.308
10	☐	☐	US 20030209739 A1	20031113	43	Vertical semiconductor device with tunnel insulator in current path controlled by gate electrode	257/278	257/E21.629; 257/E27.084; 257/E29.042
11	☐	☐	US 20030205771 A1	20031106	27	Semiconductor memory device and manufacturing method	257/390	257/E27.084; 257/E29.165; 257/E29.242

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